TOSHIBA 2SK2009

#### TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

# 2 S K 2 0 0 9

HIGH SPEED SWITCHING APPLICATIONS. ANALOG SWITCH APPLICATIONS.

High Input Impedance.

Low Gate Threshold Voltage :  $V_{th} = 0.5 \sim 1.5 V$ **Excellent Switching Times** :  $t_{on} = 0.06 \mu s$  (Typ.)

 $t_{off} = 0.12 \mu s$  (Typ.)

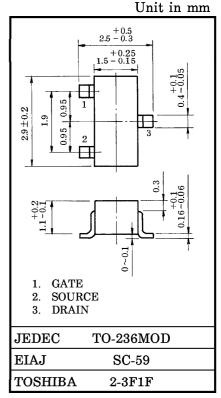
Low Drain-Source ON Resistance :  $R_{DS(ON)} = 1.2\Omega$  (Typ.)

Small Package.

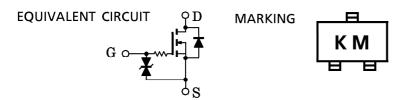
Enhancement-Mode

### MAXIMUM RATINGS (Ta = 25°C)

| CHARACTERISTIC            | SYMBOL             | RATING  | UNIT |
|---------------------------|--------------------|---------|------|
| Drain-Source Voltage      | $v_{ m DS}$        | 30      | V    |
| Gate-Source Voltage       | $v_{ m GSS}$       | ±20     | V    |
| DC Drain Current          | $I_{\mathbf{D}}$   | 200     | mA   |
| Drain Power Dissipation   | $P_{\mathbf{D}}$   | 200     | mW   |
| Channel Temperature       | ${ m T_{ch}}$      | 150     | °C   |
| Storage Temperature Range | $\mathrm{T_{stg}}$ | -55~150 | °C   |



Weight: 0.012g



THIS TRANSISTOR ELECTROSTATIC SENSITIVE DEVICE. PLEASE HANDLE WITH CAUSHON.

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## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC                 |               | SYMBOL                      | TEST CONDITION  | MIN. | TYP. | MAX. | UNIT           |
|--------------------------------|---------------|-----------------------------|---|------|------|------|----------------|
| Gate Leakage Current           |               | $I_{ m GSS}$                | $V_{GS} = \pm 10V, V_{DS} = 0$                                | _    | _    | ±0.1 | $\mu$ A        |
| Drain-Source Breakdown Voltage |               | V <sub>(BR)DSS</sub>        | $I_D=1mA, V_{GS}=0$   | 30   | _    | _    | V              |
| Drain Cut-off Cur              | rent          | $I_{ m DSS}$                | $V_{DS}=30V, V_{GS}=0$  | _    | _    | 10   | $\mu$ <b>A</b> |
| Gate Threshold Voltage         |               | $ m V_{th}$                 | $V_{ m DS}$ =3V, $I_{ m D}$ =0.1mA                            | 0.5  | _    | 1.5  | V              |
| Forward Transfer Admittance    |               | $ Y_{f_S} $                 | $V_{ m DS}$ =3V, $I_{ m D}$ =50mA                             | 100  | _    | _    | mS             |
| Drain-Source ON Resistance     |               | R <sub>DS</sub> (ON)        | $I_D=50$ mA, $V_{GS}=2.5$ V                                   | _    | 1.2  | 2    | Ω              |
| Input Capacitance              |               | $\mathrm{C}_{\mathrm{iss}}$ | $V_{DS}=3V, V_{GS}=0, f=1MHz$                                 |      | 70   |      | рF             |
| Reverse Transfer Capacitance   |               | $\mathrm{C}_{\mathrm{rss}}$ | $V_{DS}=3V, V_{GS}=0, f=1MHz$                                 | _    | 23   | _    | рF             |
| Output Capacitance             |               | $C_{OSS}$                   | $V_{DS}=3V, V_{GS}=0, f=1MHz$                                 | _    | 58   | _    | рF             |
| Switching Time                 | Turn-on Time  | $t_{on}$                    | $V_{DD} = 3V, I_{D} = 10 \text{mA}$<br>$V_{GS} = 0 \sim 2.5V$ | _    | 0.06 | _    | μs             |
|                                | Turn-off Time | $t_{	ext{off}}$             | $V_{DD} = 3V, I_{D} = 10mA$<br>$VGS = 0 \sim 2.5V$            | _    | 0.12 | _    | μs             |

#### SWITCHING TIME TEST CIRCUIT

